



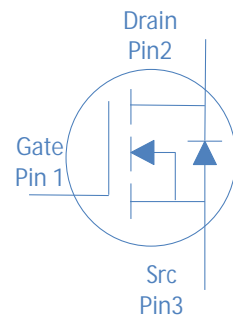
100V N-Ch Power MOSFET

Feature

- High Speed Power Switching
- Enhanced Body diode dv/dt capability
- Enhanced Avalanche Ruggedness
- 100% UIS Tested, 100% Rg Tested
- Lead Free

Application

- Synchronous Rectification in SMPS
- Hard Switching and High Speed Circuit
- Power Tools
- UPS
- Motor Control



		Conditions		
Continuous Drain Current (Silicon Limited)		c		
		c		
Continuous Drain Current (Package Limited)		c		
Pulsed Drain Current				
		c		
		c		

Thermal Resistance Junction-Case		JC		
		JA		



Fall Time

Diode Forward Voltage

Reverse Recovery Charge

F F

nC

Fig 1. Typical Output Characteristics

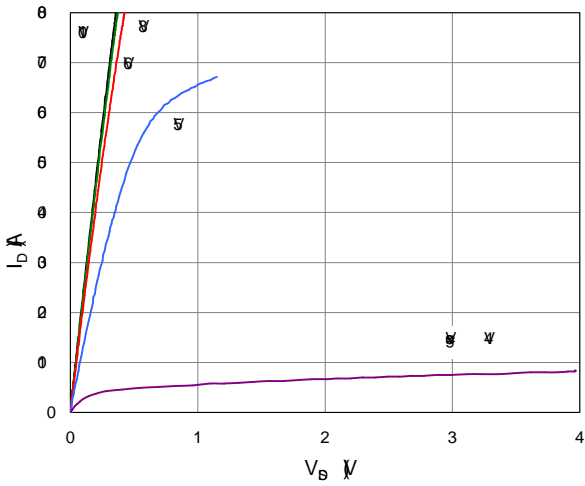


Figure 2. On-Resistance vs. Gate-Source Voltage

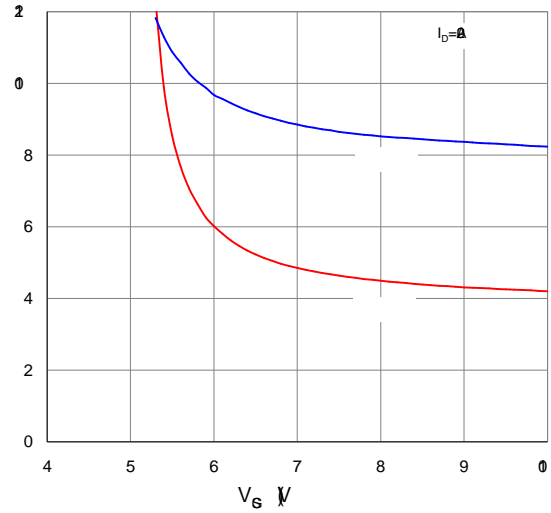


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

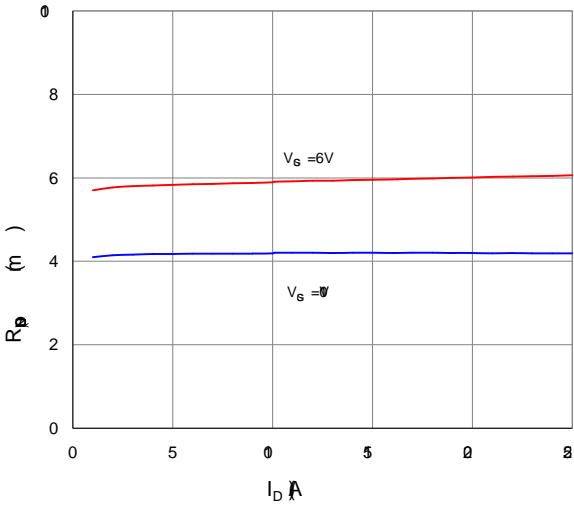


Figure 4. Normalized On-Resistance vs. Junction Temperature

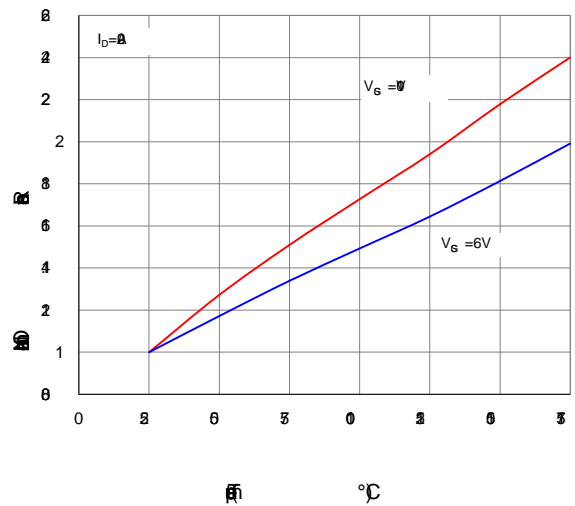


Figure 5. Typical Transfer Characteristics

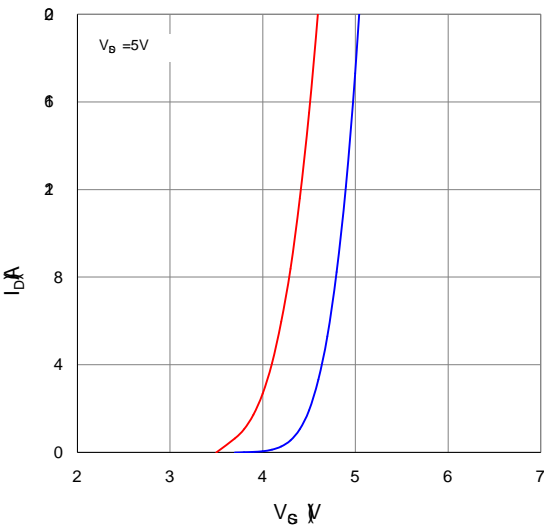


Figure 6. Typical Source-Drain Diode Forward Voltage

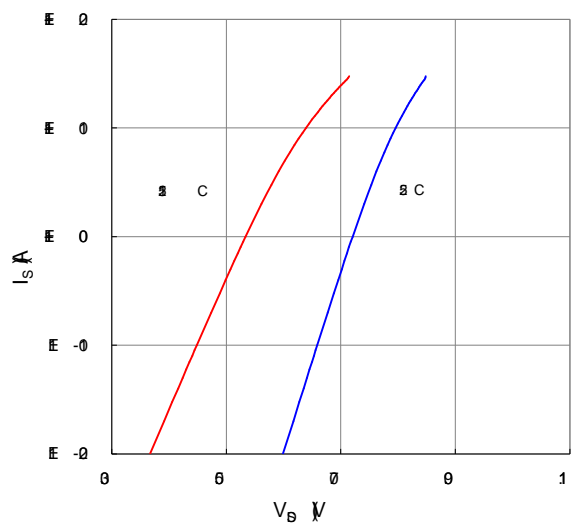




Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

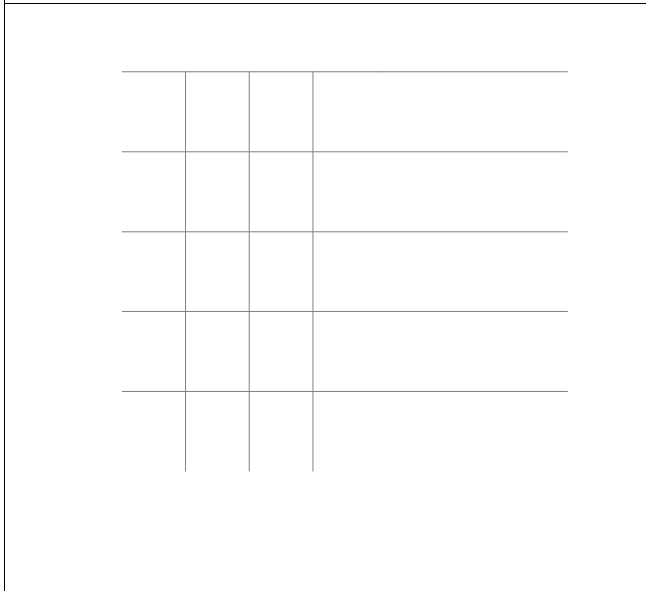


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

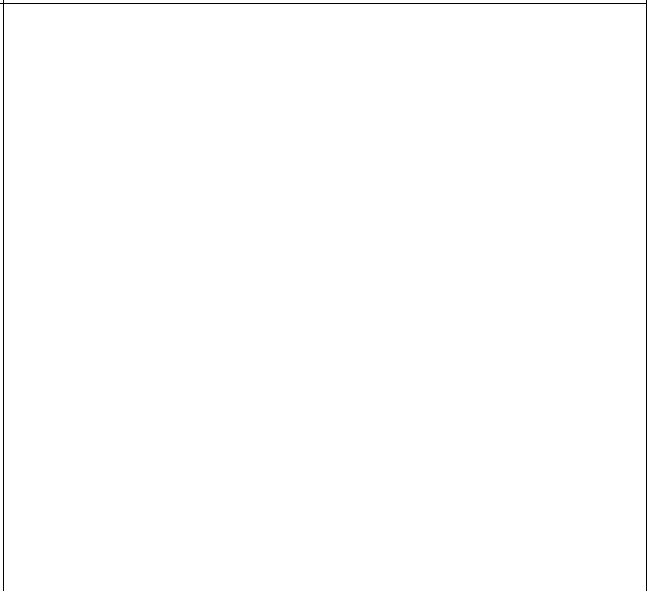


Figure 9. Maximum Safe Operating Area

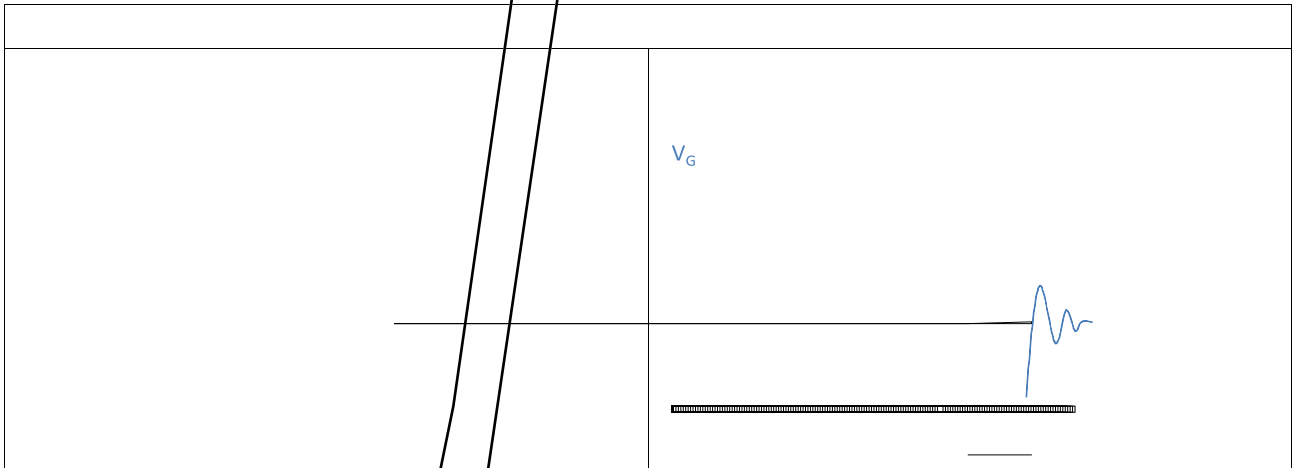


Figure 10. Maximum Drain Current vs. Case Temperature

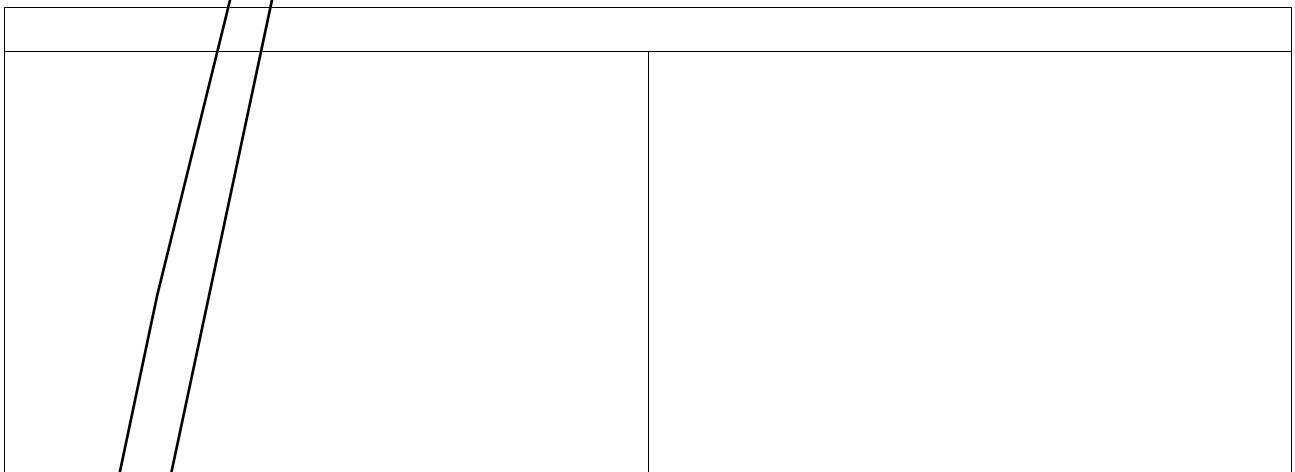
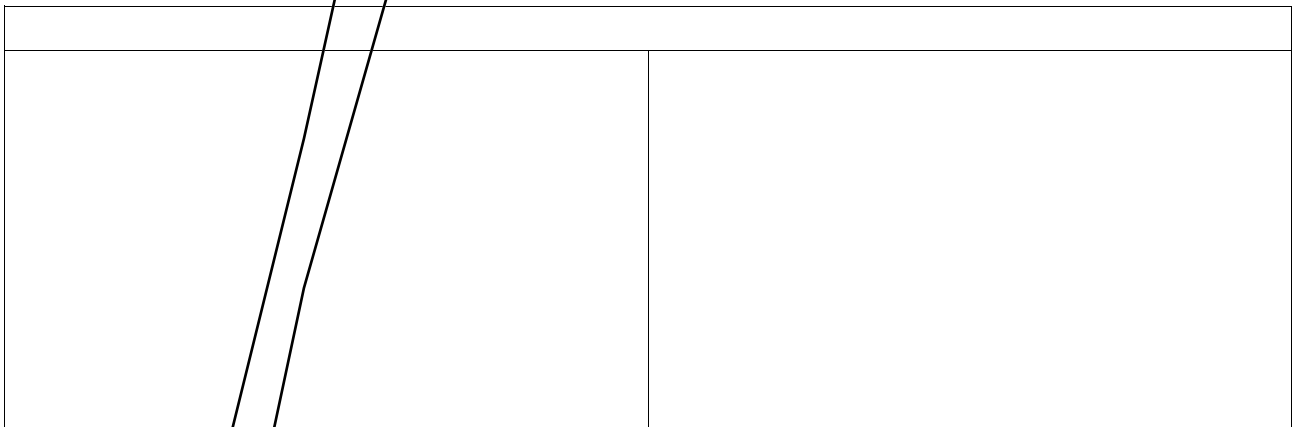
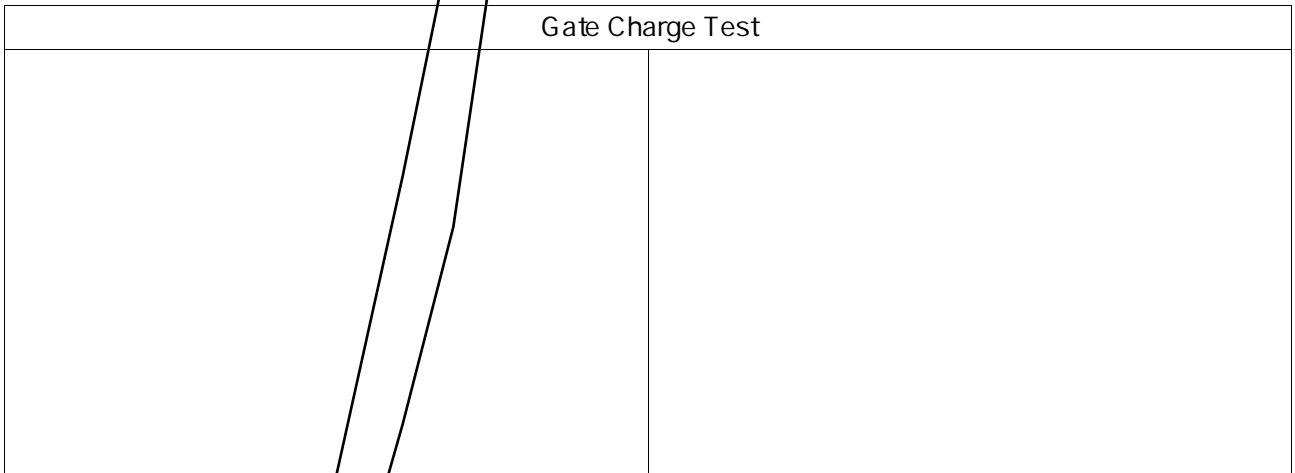


Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case





Gate Charge Test





			10.28
			15.80
C		13.48	
			0.82
			2.80
			6.80
			10.28
C	8.59		
			0.83
			5.08
F		1.28	